

Silicon NPN Power Transistors

2SC2275 2SC2275A

DESCRIPTION

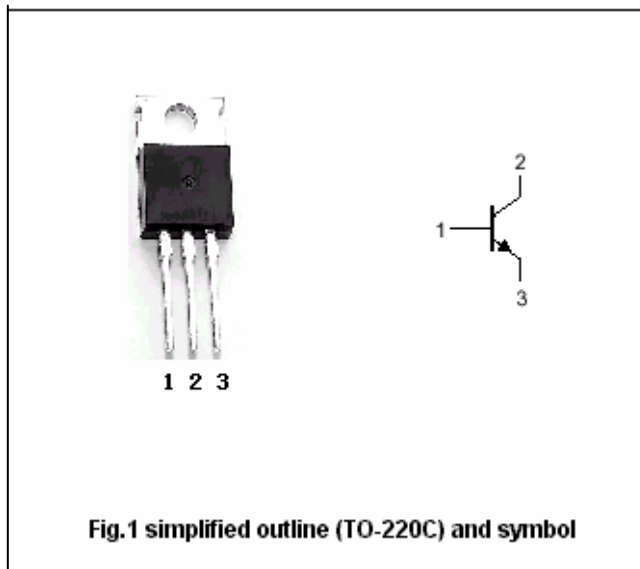
- With TO-220 package
- Complement to type 2SA985/985A
- High breakdown voltage

APPLICATIONS

- For low frequency and high frequency power amplifier applicatons

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SC2275	120	V
		2SC2275A	150	
V _{CEO}	Collector-emitter voltage	2SC2275	120	V
		2SC2275A	150	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1.5	A
I _{CM}	Collector current-peak		3.0	A
I _B	Base current		0.3	A
P _C	Collector power dissipation	T _C =25°C	25	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA, I _B =0	120			V
			150			
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A; I _B =0.1A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1A; I _B =0.1A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =120V; I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =3V; I _C =0			1.0	μA
h _{FE-1}	DC current gain	I _C =5mA; V _{CE} =5V	35			
h _{FE-2}	DC current gain	I _C =0.3A; V _{CE} =5V	60	150	320	
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V, f=1MHz		19		pF
f _T	Transition frequency	I _C =0.2A; V _{CE} =5V		200		MHz

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320

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PACKAGE OUTLINE



Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)